hardmask.

16. The method, as recited in claim 15, wherein the planarization layer is an organic planarization layer.

17. The method, as recited in claim 16, wherein the etching the self-aligned contacts/vias and the etching the trenches provide infinite metal hardmask corner selectivity.

18. The method, as recited in claim 10, wherein the thinning the planarization layer reduces an aspect ratio from at least 5:1 to less than 2:1.

19. The method, as recited in claim 10, wherein the etching the self-aligned contacts/vias and the etching the trenches provide infinite metal hardmask corner selectivity.